

Features

- Lower Series Resistance : 2.6 Ω
- Lower Capacitance : 40 fF
- Faster Switching Speed : 40 nS
- Silicon Nitride Reliability Passivation
- Polyimide Scratch Protection
- Designed for Automated Pick and Place Insertion
- Rugged by Design

Description

M/A-COM's MA4FCP Series consists of Silicon Flip Chip PIN diodes fabricated with M/A-COM's patented HMIC process. This diode is fabricated on epitaxial wafers using a process designed for repeatable electrical characteristics and extremely low parasitics. This diode is fully passivated with Silicon Nitride and has an additional layer of Polyimide for scratch protection. These protective coatings prevent damage to the junction during automated or manual handling. This flip chip configuration is suitable for pick and place insertion.

Applications

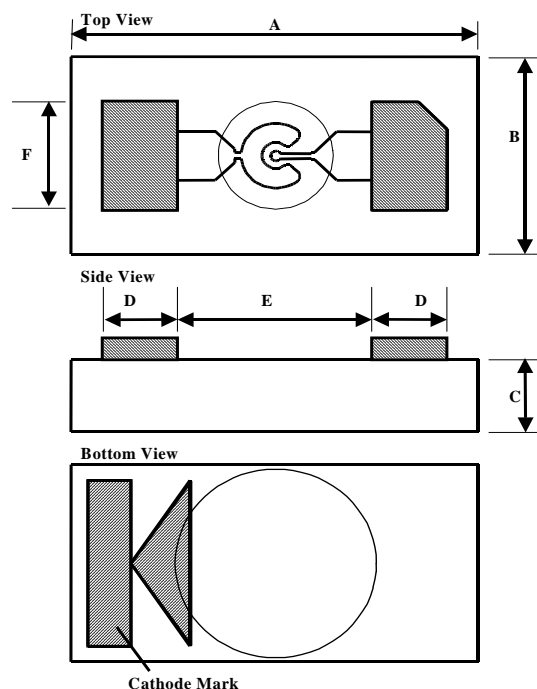
The small 0315 outline and low 0.12 pS RC product, make the device useful for multi-throw switch and switched phase shifter circuits requiring < 40 nS switching speeds up to 18 GHz operating frequency.

Absolute Maximum Ratings @ 25 °C ¹

Parameter	Absolute Maximum
Forward Current	100 mA
Reverse Voltage	- 100 V
Operating Temperature	- 55 °C to + 125 °C
Storage Temperature	- 55 °C to + 150 °C
Junction Temperature	+ 175 °C
Dissipated Power	150 mW
Mounting Temperature	+ 300 °C for 10 seconds

1. Exceeding these limits may cause permanent damage.

1269 Outline



Dim	inches		(mm)	
	min.	max.	min.	max.
A	0.0269	0.0289	0.683	0.733
B	0.0135	0.0155	0.343	0.393
C	0.0040	0.0080	0.102	0.203
D	0.0041	0.0061	0.105	0.155
E	0.0124	0.0144	0.315	0.365
F	0.0069	0.0089	0.175	0.225

Electrical Specifications @ T_A = +25°C

Parameters @ Conditions	Symbol	Units	Min.	Typ.	Max.
Total Capacitance @ -10V, 1MHz ¹	C _T	pF		0.04	0.08
Total Capacitance @ -10V, 1GHz ^{1,3}	C _T	pF		0.025	
Series Resistance @ +50mA ^{2,3} , 100MHz	R _S	Ω		2.1	2.8
Series Resistance @ +50mA ^{2,3} , 1GHz	R _S	Ω		2.6	
Forward Voltage @ +100mA	V _F	V		1.1	1.5
Reverse Voltage @ -10μA	V _R	V	-70	-100	
Reverse Current @ -40V	I _R	μA			- 10
50 – 90 % Lifetime @ + 10mA / - 6mA	TL	ns		140	
Steady State Thermal Resistance ⁴	θ	° C/W		450	

1. Total capacitance is equivalent to the sum of junction capacitance C_j and parasitic capacitance, C_p.
2. Series resistance R_S is equivalent to the total diode series resistance including the junction resistance R_j.
3. R_s and C_p measured on an HP4291A with die mounted in an ODS-186 package.
4. Steady-State Thermal Resistance measured with die mounted in an ODS-186 package.

Assembly Procedures

The following precautions should be observed to avoid damaging these devices.

Cleanliness

These devices should be handled in a clean environment. Do not attempt to clean die after installation.

ESD

These devices very susceptible to ESD and are rated Class 0 (0-199V) per HBM MIL-STD-883, method 3015.7 [C = 100pF ±10%, R = 1.5kΩ ±1%]. Even though tested die pass 100V ESD, they must be handled in a static-free environment.

General Handling

The protective polymer coating on the active areas of these devices provides scratch protection, particularly for the metal airbridge that contacts the anode. Die can be handled with tweezers or vacuum pickups and are suitable for use with automatic pick-and-place equipment.

Mounting Techniques

These devices were designed for insertion onto hard or soft substrates with the junction side down. They can be mounted with electrically conductive epoxy or with a low temperature solder preform. The die can also be assembled with the junction side up, and wire or ribbon bonds made to the pads.

Solder Die Attach using Electrically Conductive Ag Epoxy and Solder

These chips are designed to be inserted onto hard or soft substrates with the junction side down. They should be mounted onto silkscreened circuits using Electrically Conductive Ag Epoxy, approximately 1-2 mils in thickness and cured at approximately 90°C to 150 °C per manufacturer's schedule. For extended cure times > 30 minutes, temperatures must be below 200 °C.

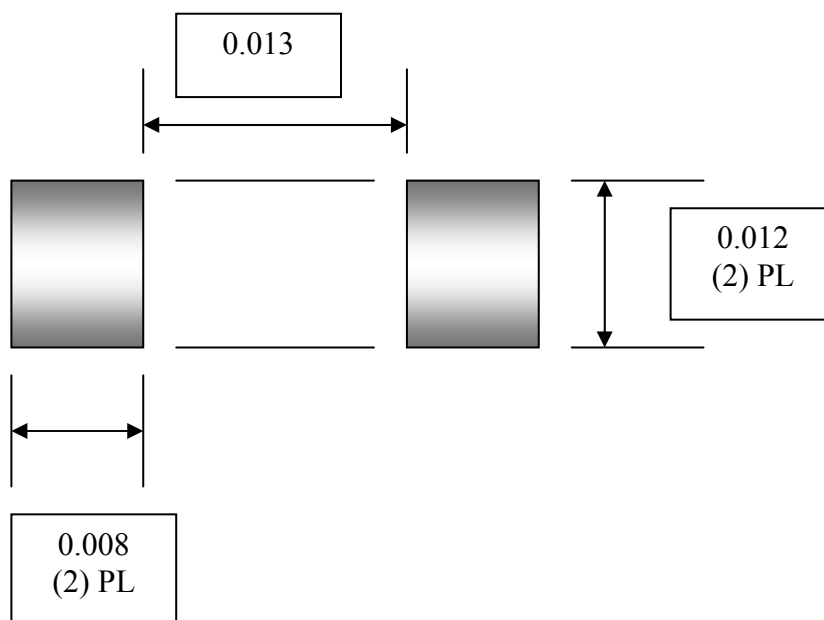
Sn Rich Solders (> 30 % by Weight) are not recommended due to the Tungsten Metallization scheme beneath the gold contacts. Indalloy or 80 Au/20 Sn Solders are acceptable. Maximum soldering temperature must be < 300 °C for < 10 seconds.

MA4FCP300

Silicon Flip Chip
PIN Diode

Rev. V1

Circuit Mounting Dimensions (Inches)



Ordering Information

Part Number	Packaging
MA4FCP300	Die in Carrier
MA4FCP300-T	Tape/Reel
MA4FCP300-W	Wafer on Frame

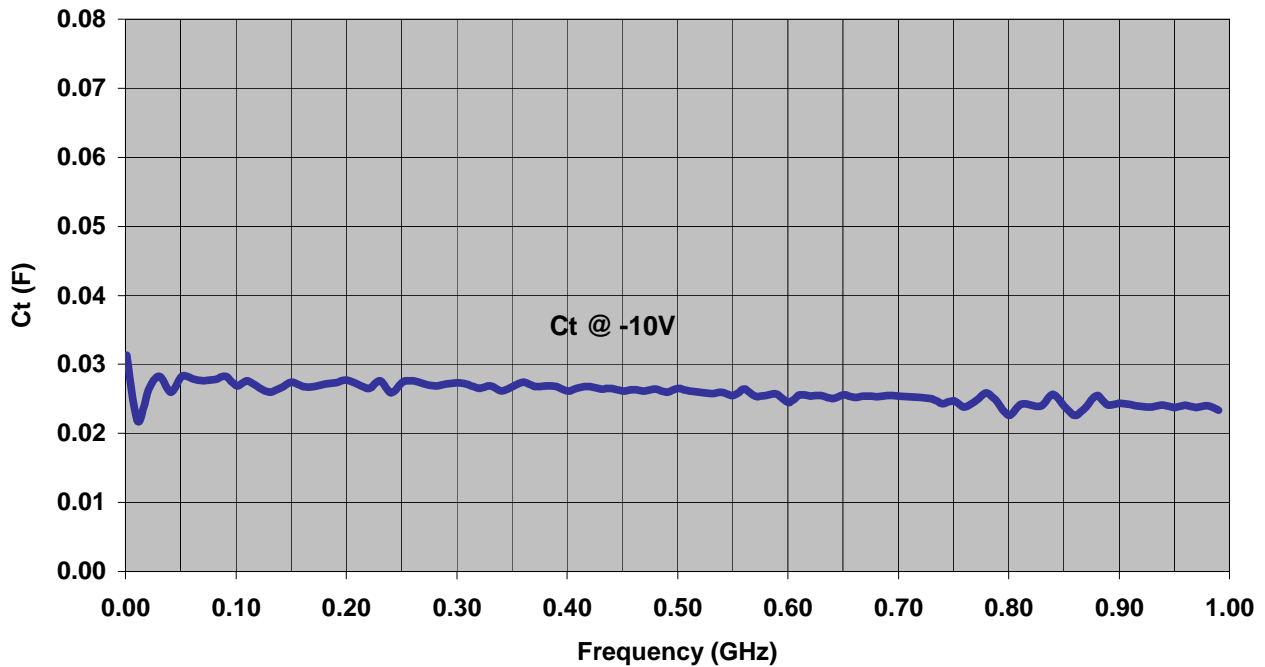
MA4FCP300



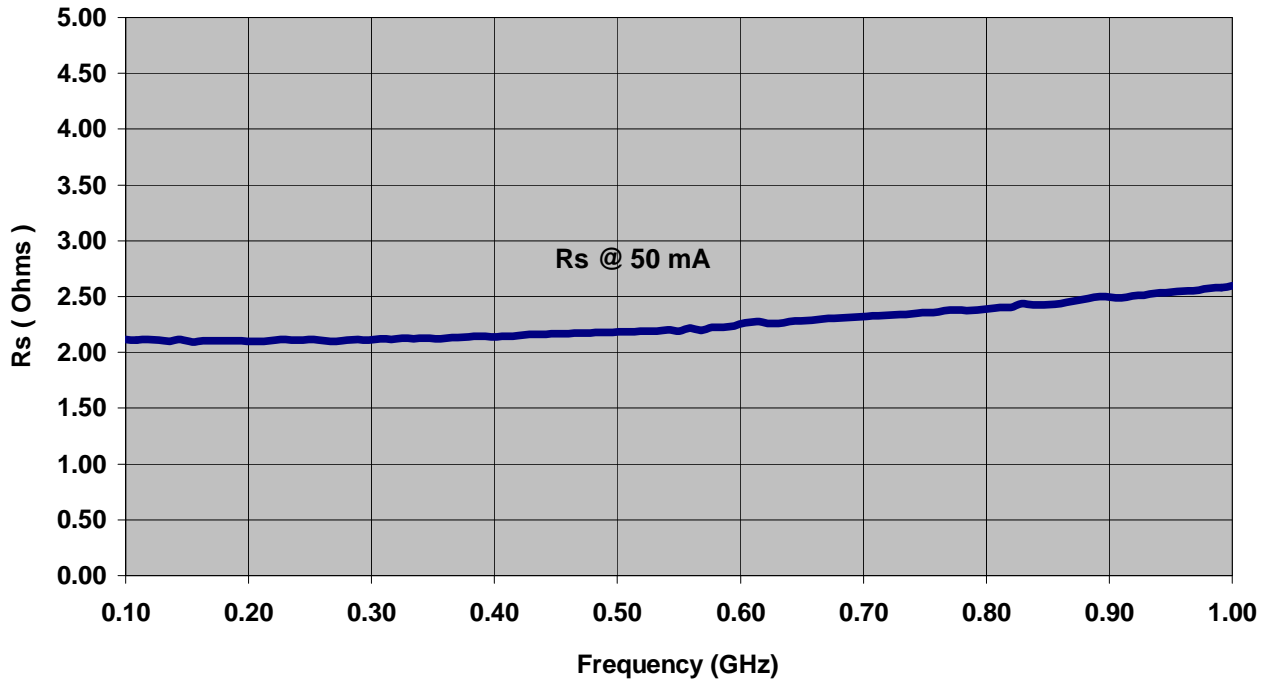
Silicon Flip Chip
PIN Diode

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Capacitance vs Frequency



Rs vs Frequency

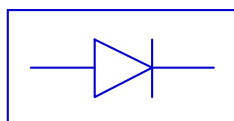
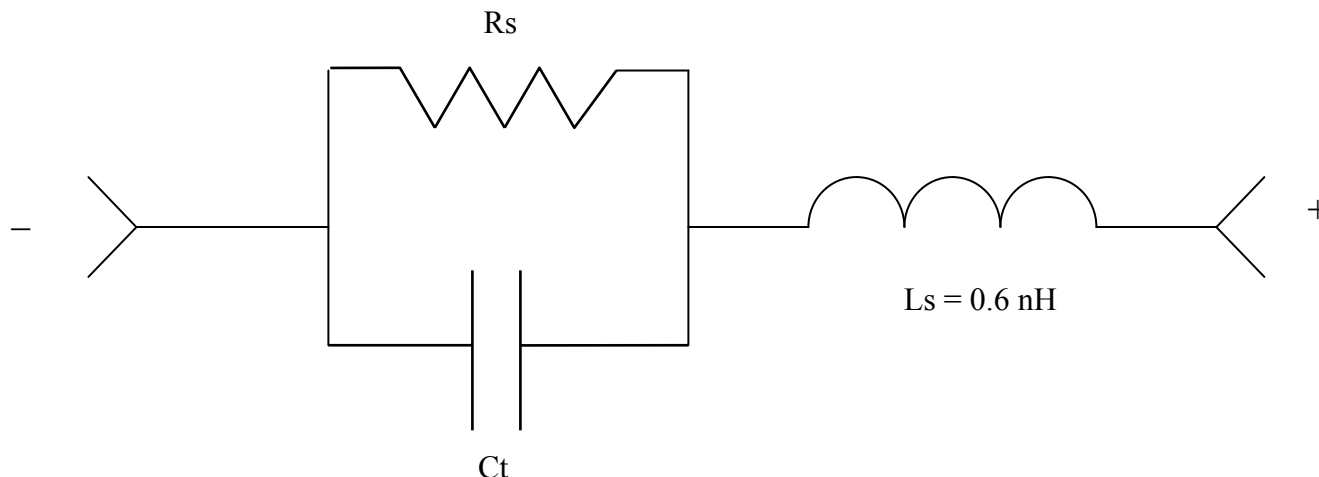


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Diode Model



MA4FCP300 SPICE Model

PinDiodeModel

NLPINM1

Is=1.0E-14 A

Vi=0.0 V

Un= 900 cm²/V-sec

Wi= 7.5 um

Rr= 20 K Ohms

Cjmin= 0.04 pF

Tau= 0.14 usec

Rs(I)= Rc + Rj(I) = 0.05 Ohm + Rj(I)

Cj0= 0.07 pF

Vj= 0.7 V

M= 0.5

Fc= 0.5

Imax= 1.0 E+5 A/m²

Kf=0.0

Af=1.0

wBv= 100 V

wPmax= 125 mW

Ffe= 1.0

AllParams=